

March 2014

FGL60N100BNTD 1000 V, 60 A NPT Trench IGBT

Features

- · High Speed Switching
- Low Saturation Voltage: V_{CE(sat)} = 2.5 V @ I_C = 60 A
- · High Input Impedance
- · Built-in Fast Recovery Diode

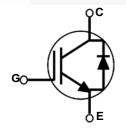
Applications

UPS, Welder

General Description

Using Fairchild's proprietary trench design and advanced NPT technology, the 1000V NPT IGBT offers superior conduction and switching performances, high avalanche ruggedness and easy parallel operation. This device offers the optimum performance for hard switching application such as UPS, welder applications.





Absolute Maximum Ratings

Symbol	Description		Ratings	Unit
V _{CES}	Collector to Emitter Voltage		1000	V
V_{GES}	Gate to Emitter Voltage		± 25	V
	Collector Current	@ T _C = 25°C	60	А
I _C	Collector Current	@ T _C = 100°C	42	А
I _{CM (1)}	Pulsed Collector Current	@ T _C = 25°C	200	A
l _F	Diode Continuous Forward Current	@ T _C = 100°C	15	А
P _D	Maximum Power Dissipation	@ T _C = 25°C	180	W
	Maximum Power Dissipation	@ T _C = 100°C	72	W
T _J	Operating Junction Temperature		-55 to +150	°C
T _{stg}	Storage Temperature Range		-55 to +150	°C
T _L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 second	300	°C	

Notes:
1: Repetitive rating: Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Ratings	Unit
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction to Case	0.69	°C/W
$R_{\theta JC}(Diode)$	Thermal Resistance, Junction to Case	2.08	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	25	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FGL60N100BNTD	FGL60N100BNTD	TO-264	Tube	N/A	N/A	30

Electrical Characteristics of the IGBT $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					
BV _{CES}	Collector to Emitter Breakdown Voltage	$V_{GE} = 0 \text{ V}, I_{C} = 1 \text{ mA}$	1000	-	-	V
I _{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0 V$	-	-	1	mA
I _{GES}	G-E Leakage Current	$V_{GE} = V_{GES}$, $V_{CE} = 0 V$	-	-	±500	nA
On Charac	teristics					
V _{GE(th)}	G-E Threshold Voltage	I_C = 60 mA, V_{CE} = V_{GE}	4.0	5.0	7.0	V
		I _C =10 A, V _{GE} = 15 V	-	1.5	1.8	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	I _C = 60 A, V _{GE} = 15 V,	-	2.5	2.9	V
Dynamic C	haracteristics					
C _{ies}	Input Capacitance		-	6000	-	pF
C _{oes}	Output Capacitance	V _{CE} = 10 V _, V _{GE} = 0 V, f = 1MHz	-	260	-	pF
C _{res}	Reverse Transfer Capacitance	TWITE	-	200	-	pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time		-	140	-	ns
t _r	Rise Time	$V_{CC} = 600 \text{ V}, I_{C} = 60 \text{ A},$ $R_{G} = 51 \Omega, V_{GE} = 15 \text{ V},$	-	320	-	ns
t _{d(off)}	Turn-Off Delay Time	Inductive Load, $T_C = 25^{\circ}C$	-	630	-	ns
t _f	Fall Time		-	130	-	ns
Qg	Total Gate Charge		-	275	-	nC
Q _{ge}	Gate to Emitter Charge	$V_{CE} = 600 \text{ V}, I_{C} = 60 \text{ A},$ $V_{GF} = 15 \text{ V}, T_{C} = 25^{\circ}\text{C}$	-	45	-	nC
Q _{gc}	Gate to Collector Charge	GE 10 V, 1C - 20 0	-	95	-	nC

Electrical Characteristics of the Diode $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max	Unit
V _{FM}	Diode Forward Voltage	I _F = 15 A	1	1.2	1.7	V
		I _F = 60 A	-	1.8	2.1	V
t _{rr}	Diode Reverse Recovery Time	I _F = 60 A, di/dt = 20 A/us	-	1.2	1.5	us
I _R	Instantaneous	V _{RRM} = 1000 V	-	0.05	2.0	uA

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

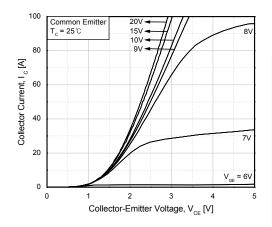


Figure 3. Saturation Voltage vs. Case
Temperature at Variant Current Level

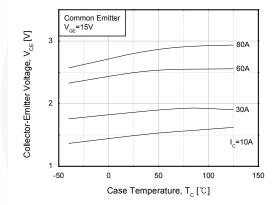


Figure 5. Saturation Voltage vs. V_{GE}

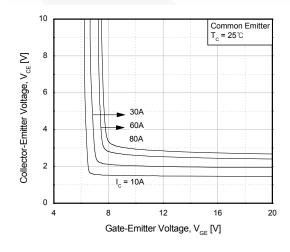


Figure 2. Typical Saturation Voltage Characteristics

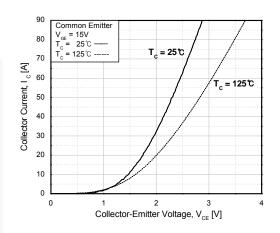


Figure 4. Saturation Voltage vs. V_{GE}

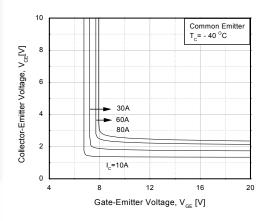
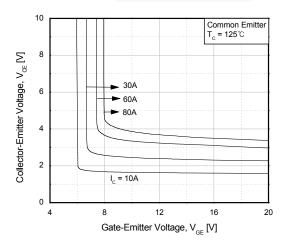


Figure 6. Saturation Voltage vs. V_{GE}



Typical Performance Characteristics

Figure 7. Capacitance Characteristics

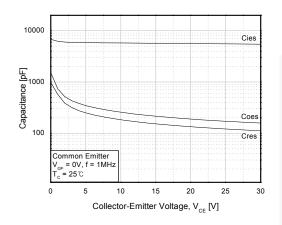


Figure 9. Switching Characteristics vs. Collector Current

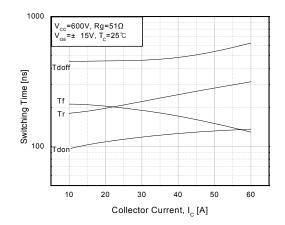


Figure 11. SOA Characteristics

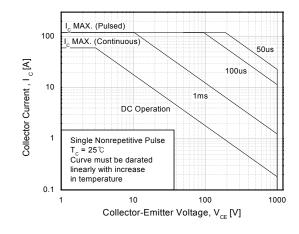


Figure 8. Switching Loss vs. Gate Resistance

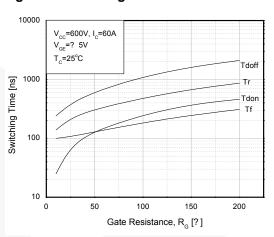


Figure 10. Gate Charge Characteristics

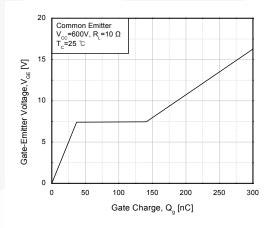
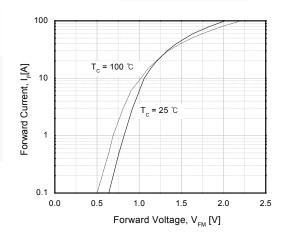
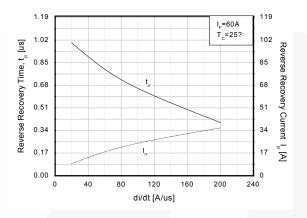


Figure 12. Forward Characteristics



Typical Performance Characteristics

Figure 13. Reverse Recovery Characteristics Figure 14. Reverse Recovery Characteristics vs. di/dt Figure 14. Reverse Recovery Characteristics vs. Forward Current



vs. Forward Current

1.2 di/dt=-20A/us
T_c=25?

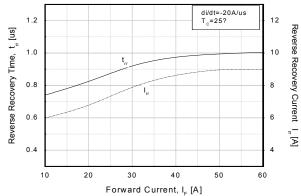
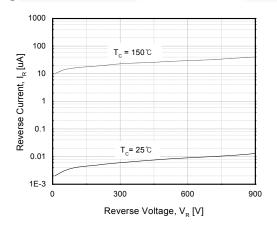


Figure 15. Reverse Current vs. Reverse Voltage Figure 16. Junction Capacitance



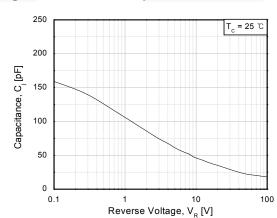
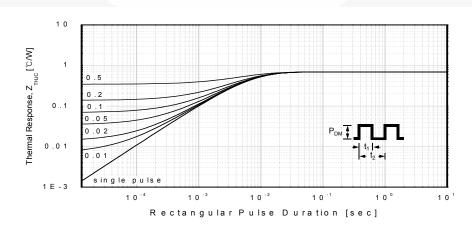


Figure 17. Transient Thermal Impedance of IGBT



Mechanical Dimensions 18.30 5.20 20.20 17.70 Α В 4.80 19.80 16.60 (1.00) (2.00) (12.00 Ø3.50 3.10 ⊕ 0.254 A B R2.00 C 1.20 9.10 C 8.90 21.62 21.02 0.50 20.20 19.80 R1.00 C 1.70 (1.50) 2.60 2.40 (4.05)-3.20 2.80 1.50) 3.10 2.50 (1.50) € 2.70 2X 20.50 C **∠**c\ ⊕ 0.254 (M) A B 5.75 5.15 0.85 **FRONT VIEW** SIDE VIEW **BACK VIEW** NOTES: A. PACKAGE REFERENCE: JEDEC TO264 5.20 3.70 VARIATION AA. B. ALL DIMENSIONS ARE IN MILLIMETERS. (0.15) 4.80 OUT OF JEDEC STANDARD VALUE. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994. DIMENSIONS ARE EXCLUSIVE OF BURRS E. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS. F. THIS PACKAGE IS INTENDED ONLY FOR "FS PKG CODE AR" G. DRAWING FILE NAME: TO264A03REV1 **BOTTOM VIEW**

Figure 18. TO-264 3L - 3LD; TO264; MOLDED; JEDEC VARIATION AA

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